

## **CLAIM AMENDMENT**

Claims 22 – 24, 28, 29 and 31 have been amended, claims 32-35 have been added, and claims 1-21 have been canceled.

Claim 1-21(Canceled).

Claim 22 (currently amended): A method of forming a semiconductor chip, comprising:

providing a substrate having a main surface, the main surface including a ~~flame-shaped~~ frame-shaped first area, which is along sides of the main surface, and a second area encompassed by the first area;

forming a pad in the first area;

forming a bump electrode on the pad; and

forming at least one supporting member ~~on~~ in the second area, the support member being formed of resin material.

Claim 23 (currently amended): A method of forming a semiconductor chip as claimed in claim 22, wherein ~~forming the support member includes~~

~~forming the supporting member of resin material~~ forming at least one support member includes forming a plurality of supporting members.

Claim 24 (currently amended): A method of forming a semiconductor chip, comprising:

providing a substrate having a main surface, the main surface including a frame-shaped first area, which is along sides of the main surface, and a second area encompassed by the first area;

forming a pad in the first area;

forming a bump electrode on the pad; and

forming at least one supporting member in the second area. ~~A method of forming a semiconductor chip as claimed in claim 22, wherein forming the supporting member and the bump electrode includes forming the supporting member and the bump electrode of the same material.~~

Claim 25 (original): A method of forming a semiconductor chip as claimed in claim 24, wherein forming the pad includes forming the pad to have a second thickness, forming the bump electrode includes forming the bump

electrode to have a third thickness and forming the support member includes forming the support member to have a first thickness, which is substantially equals to the sum of the second and third thicknesses.

Claim 26 (original): A method of forming a semiconductor chip as claimed in claim 24, wherein forming the pad includes forming the pad to have a second thickness, forming the bump electrode includes forming the bump electrode to have a third thickness and forming the support member includes forming the support member to have a first thickness, which is less than the sum of the second and third thicknesses.

Claim 27 (original): A method of forming a semiconductor chip as claimed in claim 24, further comprising, forming a resin connector on the support member.

Claim 28 (currently amended): A method of forming a semiconductor package, comprising:

providing a substrate having a main surface, the main surface including

a ~~flame-shaped~~ frame-shaped first area, which is along sides of the main surface, and a second area encompassed by the first area;

forming a pad in the first area;

forming a bump electrode on the pad;

forming at least one supporting member on the second area, the support member having a tip;

providing a tape substrate having a land electrode;

connecting the bump electrode to the land electrode; and

connecting the tip of the supporting member to the tape substrate.

Claim 29 (currently amended): A method of forming a semiconductor package as claimed in claim 28, wherein connecting the tip of the supporting member to the tape substrate includes connecting the tip of the supporting member to the tape substrate by a connector resin.

Claim 30 (original): A method of forming a semiconductor package as claimed in claim 28, wherein the tape substrate further includes a dummy land electrode, and connecting the supporting member to the tape substrate includes

connecting the supporting member to the tape substrate by connecting the tape substrate to the dummy land electrode.

Claim 31 (currently amended): A method of forming a semiconductor package, comprising:

providing a semiconductor chip including a main substrate having a main surface, the main surface including a ~~flame-shaped~~ frame-shaped first area, which is along sides of the main surface, and a second area encompassed by the first area, a pad formed in the first area, a bump electrode formed on the pad, and at least one supporting member formed on the second area;

preparing an assemble apparatus having a recess at its center;

providing a tape substrate having a land electrode;

placing the tape substrate on the assemble apparatus wherein an area on the tape substrate, which is encompassed by the land electrode, is disposed on the recess of the assemble apparatus; and

mounting the semiconductor chip on the tape substrate, and connecting the bump electrode to the land electrode.

Claim 32 (new): A method of forming a semiconductor chip as claimed in claim 22, wherein forming at least one supporting member in the second area includes forming the supporting member in a center of the second area.

Claim 33 (new): A method of forming a semiconductor chip as claimed in claim 24, further comprising:

forming a first barrier metal formed under the bump electrode; and  
forming a second barrier metal formed under the supporting member,  
the first and second barrier metals being formed of the same material, and the first and second barrier metals having the same thickness.

Claim 34 (new): A method of forming a semiconductor package as claimed in claim 30, further comprising:

forming a solder ball on the dummy land electrode,  
wherein the supporting member is connected to the tape substrate by the solder ball.

Claim 35 (new): method of forming a semiconductor package as claimed

in claim 30, wherein the dummy land electrode is arranged under the supporting member.